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connections comprise a material with low thermal conductivity.

20. (New) Device according to claim 17, in which each of the mechanical connections are in line with two mechanical support devices, each belonging to one of two neighboring detectors.

21. (New) Device according to claim 17 in which the said device forms a repetitive detector configuration according to a linear or matrix architecture.

22. (New) A process for manufacturing a device according to claim 17 which, starting from a processing circuit with metallic contact blocks visible on the surface, comprises the following steps:

(a) forming a reflector on a surface of the processing circuit through deposit of a metallic coat with definition through photolithography;

(b) forming an optical cavity through deposit of a sacrificial layer which is later removed;

whereby at least two layers constituting the microbridge are laid, one of said layers being a layer of heat-sensitive material, and another of said layers being a conducting coat constituting the detector electrodes;

(c) forming the mechanical support and the electrical interconnection devices which are made against the contact blocks, by etching of the sacrificial layer, the layer of heat sensitive material and the conducting coat, and by depositing and etching at least one metallic coat which provides the electrical and mechanical continuity between the contact blocks and the microbridge electrodes;

(d) forming the detector electrodes defined by etching the conducting coat; and

(e) forming the layer of heat-sensitive material, the conducting coat and optional

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layers by etching simultaneously using a mask to shield a zone located between the detectors.

23. (New) The process according to claim 22, in which the layer of heat-sensitive material is a layer of amorphous silicon.

24. (New) The process according to claim 22, in which the conducting coat constituting the detector electrodes is a layer of titanium nitride.

25. (New) The process according to claim 22 in which a layer of aluminium is deposited to provide the electrical continuity between the electric blocks and the microbridge electrodes.

26. (New) The process according to claim 22, in which the metallic coat constituting the detector electrodes, is removed in the zones occupied by the mechanical connections

27. (New) The process according to claim 22 in which, after the definition stage of the detector electrodes by etching of the conducting coat, a final layer is deposited.

28. (New) The process according to claim 27 in which the final layer is a layer of material selected from the group consisting of silicon dioxide, silicon nitride, amorphous silicon and mixtures thereof.

29. (New) The process according to claim 22 in which the mechanical connections are fined down due to partial etching of these connections.

30. (New) The process according to claim 29 in which the conducting coat and the final layer are removed at the connections.

31. (New) The process according to claim 22 in which a connection element of a material with a low thermal conductivity is added on the microbridges entirely isolated